**Product data sheet** 

# 1. Product profile

### 1.1 General description

Silicon N-channel enhancement mode LDMOS transistor encapsulated in a 2-lead flangeless package (SOT538A) with a ceramic cap. The common source is connected to the mounting base.

Table 1. Typical performance

RF performance at Th = 25 °C in a common source test circuit.

Mode of operation	f	V <sub>DS</sub>	PL	G <sub>p</sub>
	(MHz)	(V)	(W)	(dB)
Pulsed class-AB; $t_p$ = 50 $\mu$ s; $\delta$ = 2%	1030 to 1090	36	2	>16

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features and benefits

- High power gain
- Easy power control

- Excellent ruggedness
- Source on mounting base eliminates DC isolators, reducing common mode inductance.

### 1.3 Applications

Avionics applications in the 1030 to 1090 MHz frequency range.

# 2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	drain		,
2	gate		1   <u> </u>
3	source, connected to mounting base	3	2 3 3 sym112



# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLA1011-2	-	ceramic surface mounted package; 2 leads	SOT538A	

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	75	V
$V_{GS}$	gate-source voltage		-	±15	V
I <sub>D</sub>	drain current (DC)		-	2.2	Α
P <sub>tot</sub>	total power dissipation	$T_h \leq 25~^{\circ}C$		10	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{th(j\text{-}mb)}$	thermal impedance from junction to mounting base		Ш 1	K/W
$R_{th(mb-h)}$	thermal resistance from mounting base to heatsink		[2] 6.5	K/W

<sup>[1]</sup> Thermal impedance is determined under RF operating conditions with pulsed bias and  $T_h = 25 \, ^{\circ}\text{C}$ .

### 6. Characteristics

Table 6. Characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$ ; $I_{D} = 0.2$ mA	75	-	-	V
$V_{GSth}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 20 \text{ mA}$	2	-	5	V
I <sub>DSS</sub>	drain-source leakage current	$V_{GS} = 0; V_{DS} = 26$	-	-	0.1	mA
I <sub>DSX</sub>	on-state drain current	$V_{GS} = V_{GSth} + 9 V;$ $V_{DS} = 10 V$	2.8	-	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS} = \pm 15 \text{ V}; V_{DS} = 0$	-	-	40	nA

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<sup>[2]</sup> Typical value for mounting on PCB with 32 0.4 mm thermal vias with 20 μm tin plating and thermal compound between PCB and heatsink.

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**Table 6.** Characteristics ...continued  $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 0.75 \text{ A}$	-	0.5	-	S
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 0.75 \text{ A}$	-	1.2	-	Ω
C <sub>is</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 26 \text{ V}; f = 1 \text{ MHz}$	-	11	-	pF
C <sub>os</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 26 \text{ V}; f = 1 \text{ MHz}$	-	9	-	pF
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 26 \text{ V}; f = 1 \text{ MHz}$	-	0.5	-	pF

# 7. Application information

Table 7. RF performance in a common source class-AB circuit

 $T_h = 25$  °C;  $R_{th \, mb\text{-}h} = 6.5$  K/W unless otherwise specified.

Mode of operation	f	V <sub>DS</sub>	I <sub>DQ</sub>	$P_L$	$G_p$	t <sub>r</sub>	t <sub>f</sub>	Pulse droop
	(MHz)	(V)	(mA)	(W)	(dB)	(ns)	(ns)	(dB)
Pulsed class-AB; $t_p$ = 50 $\mu$ s; $\delta$ = 2%	1030 to 1090	36	50	2	>16	<15	<15	<0.5

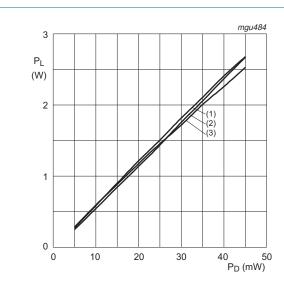
# 7.1 Ruggedness in class-AB operation

The BLA1011-2 is capable of withstanding a load mismatch corresponding to VSWR = 5: 1 through all phases under the operating conditions.

Table 8. Typical impedance values

Frequency	Z <sub>S</sub>	Z <sub>L</sub>
(MHz)	$(\Omega)$	$(\Omega)$
1030	1.51 + j 11.76	6.9 + j 5
1060	1.51 + j 11.26	6.7 + j 5.9
1090	1.52 + j 10.77	5.1 + j 6.6

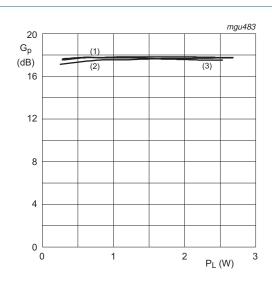
#### **Avionics LDMOS transistor**



 $T_h = 25 \, ^{\circ}\text{C}; V_{DS} = 36 \, \text{V}; I_{DQ} = 50 \, \text{mA}; \text{class-AB}; t_p = 50 \, \text{us}; \delta = 2\%$ 

- (1) f = 1060 MHz.
- (2) f = 1030 MHz.
- (3) f = 1090 MHz.

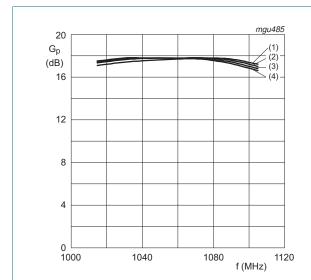
Fig 1. Load power as a function of drive power; typical values.



 $T_h$  = 25 °C;  $V_{DS}$  = 36 V;  $I_{DQ}$  = 50 mA; class-AB;  $t_p$  = 50  $\mu$ s;  $\delta$  = 2%.

- (1) f = 1060 MHz.
- (2) f = 1030 MHz.
- (3) f = 1090 MHz.

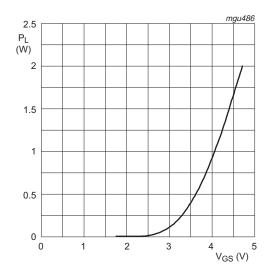
Fig 2. Power gain as a function of load power; typical values.



 $T_h$  = 25 °C;  $V_{DS}$  = 36 V;  $I_{DQ}$  = 50 mA; class-AB;  $t_p$  = 50  $\mu s;$   $\delta$  = 2%.

- (1)  $P_L = 1 W$ .
- (2)  $P_L = 2 W$ .
- (3)  $P_L = 3 W$ .
- (4)  $P_L = 4 W$ .

Fig 3. Power gain as a function of frequency; typical values.

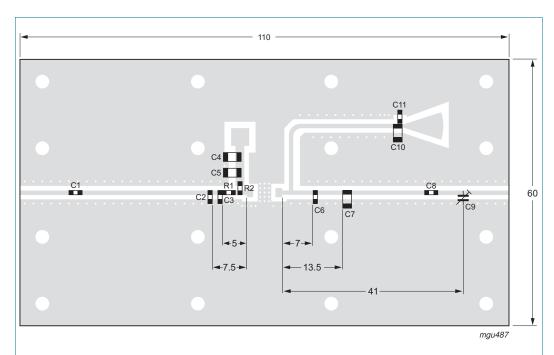


 $T_h$  = 25 °C;  $V_{DS}$  = 36 V;  $I_{DQ}$  = 50 mA; class-AB; f = 1090 MHz;  $t_p$  = 50  $\mu s;$   $\delta$  = 2%.

Fig 4. Load power as a function of gate-source voltage; typical values.

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#### **Avionics LDMOS transistor**



Dimensions in mm.

The components are situated on one side of the Rogers 6006 printed-circuit board (thickness = 0.64 mm;  $\epsilon_r$  = 6.2), the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by through-metallization.

Fig 5. Printed-circuit board for class-AB test circuit.

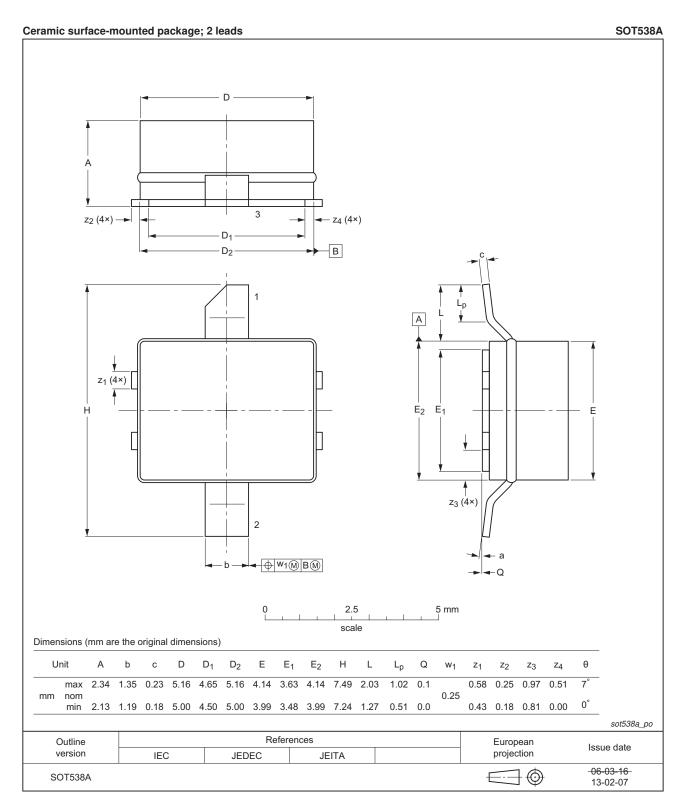
# 8. Test information

Table 9.List of components for class-AB test circuit(see Figure 5)

Component	Description		Value
C1, C8	multilayer ceramic chip capacitor	[1]	56 pF
C2	multilayer ceramic chip capacitor	[1]	7.5 pF
C3	multilayer ceramic chip capacitor	[1]	1.8 pF
C4, C10	multilayer ceramic chip capacitor	[2]	20 nF
C5	multilayer ceramic chip capacitor	[3]	33 pF
C6	multilayer ceramic chip capacitor	[1]	5.6 pF
C7	multilayer ceramic chip capacitor	[3]	6.2 pF
C9	tekelec trimmer; type 37283		0.4 to 2.5 pF
C11	multilayer ceramic chip capacitor	[1]	33 pF
R1	SMD resistor		2.2 $\Omega$ (2 in parallel)
R2	SMD resistor		22 Ω

- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 200B or capacitor of same quality.
- [3] American Technical Ceramics type 100B or capacitor of same quality.

# Package outline



Package outline SOT538A Fig 6.

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# 10. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLA1011-2 v.6	20130506	Product data sheet	-	BLA1011-2 v.5	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Package outline drawings have been updated to the latest version.</li> </ul>				
BLA1011-2 v.5	20031119	Product specification	-	BLA1011-2 v.4	

#### **Avionics LDMOS transistor**

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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